

oxidizing the porous silicon layer to form a layer of porous silicon dioxide;
forming an extraction grid on the porous silicon dioxide layer;
etching openings through the porous silicon dioxide and the extraction grid; and
forming emitters in the openings in the porous silicon dioxide and the extraction

grid.

45. (Amended) The method of claim 42 further comprising planarizing the silicon dioxide layer.

52. (Amended) A method of fabricating a porous dielectric layer in a field emission display comprising:

forming a polycrystalline silicon layer on a substrate and a plurality of columns on the substrate;

forming pores in the polycrystalline silicon layer to form a layer of porous silicon having a porosity of greater than 50%; and

oxidizing the polycrystalline silicon layer to provide a porous silicon dioxide layer.

22/56. (Twice Amended) A method of fabricating a field emission display baseplate-comprising:

forming conductors on a substrate;

forming a porous silicon dioxide layer to form a layer of porous silicon dioxide having a porosity of greater than 22.5% on the conductors and on the substrate, the porous silicon dioxide layer comprising columnar spacers of silicon dioxide with pores between the columnar spacers;

forming an extraction grid on the porous silicon dioxide layer;

etching openings through the silicon dioxide and the extraction grid; and

forming emitters in the openings in the porous silicon dioxide and the extraction

grid.

B5 ~~62~~. (Amended) The method of claim ~~42~~ wherein the act of oxidizing the porous silicon layer forms a porous silicon dioxide layer having at least 22.5% voids.

B6 ~~66~~. (Amended) The method of claim ~~46~~ wherein the act of oxidizing the porous polycrystalline silicon layer forms a porous silicon dioxide layer having at least 22.5% voids.

B7 71. (Amended) The method of claim ~~53~~ wherein the act of oxidizing the porous polycrystalline silicon layer forms a porous silicon dioxide layer having at least 22.5% voids.

B8 79. (Amended) The method of claim ~~56~~ further comprising planarizing the silicon dioxide layer.

REMARKS

Claims 42-84 are pending in this divisional application. In the Office Action dated July 8, 2002, the Examiner rejected claim 52 under 35 U.S.C. § 102(b) as being anticipated by U.S. Patent No. 5,529,524 to Jones. Claims 52-55 were rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 5,458,518 to Lee in view of Jones. Claims 42-46, 49, 50, 56, 59, 60, and 62-84 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Lee in view of Jones further in view of U.S. Patent No. 5,569,058 to Gnade *et al.* The Examiner further rejected claims 47, 48, 51, 57, 58 and 61 under 35 U.S.C. § 103(a) as being unpatentable over Lee, Jones '524, and Gnade *et al.* further in view of U.S. Patent No. 5,663,608 to Jones *et al.* Applicants disagree with these grounds of rejection and wish to clarify various distinctions of Applicants' invention over the cited art. Reconsideration is therefore requested in light of the present amendment and following remarks.

The disclosed embodiments of the invention will now be discussed in comparison to the prior art. Of course, the discussion of the disclosed embodiments, and the discussion of

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